

### 14-Stage Binary Ripple Counter / Divider with Oscillator in bare die form

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### Description

The 74HC4060 is produced on a 2.5µm 5V CMOS process with high speed LSTTL performance combined with CMOS low power consumption. The device consists of 14 master—slave flip—flops & an oscillator with frequency controlled either by crystal or by external RC circuit. Each flip—flop output feeds the next where each output frequency is half the preceding one. A high-to-low transition on the clock input increments the counter. The active—high Reset is asynchronous & disables the oscillator for low standby power consumption. Ten kinds of divided output are provided; 4 to 10 & 12 to 14 stage inclusive. Maximum division available at Q12 is 1/16384 of oscillator frequency.

### **Ordering Information**

The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see <u>54HC4060</u>

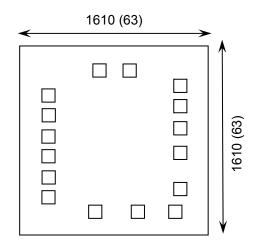
## Supply Formats:

- Defaut Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

### Features:

- Output Drive Capability: 10 LSTTL Lyads
- Low Input Current: 1µA
- Outputs directly interface CNCS NMOS and TTL
- Operating Voltage Range: 2 to 6V
- CMOS High Noise Impunity
- Function compatible with CD4060B.

### Die Dimensions in μm (mils)



## **Mechanical Specification**

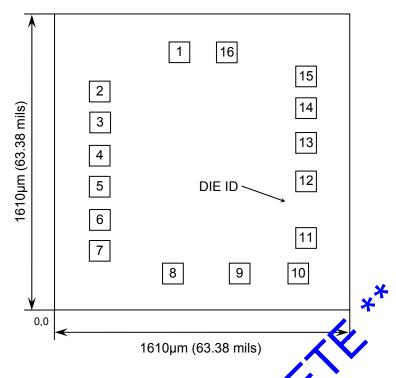
Die Size (Unsawn)	1610 x 1610 63 x 63	µm mils
Minimum Bond Pad Size	110 x 110 4 x 4	μm mils
Die Thickness	350 (±20) 13.78 (±0.79)	μm mils
Top Metal Composition	Al 1%Si 1.1μ	m
Back Metal Composition	N/A – Bare S	Si





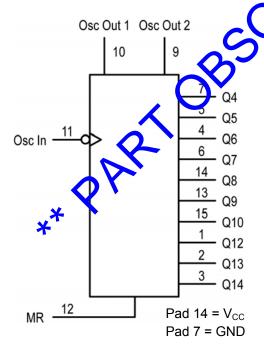
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## Pad Layout and Functions



PAD	FUNCTION	COORDIN	ATES (mm)	
FAD	FUNCTION	Х	/ Y	
1	Q12	0.610	1.350	
2	Q13	0.190	1.140	
3	Q14	0.190	0.970	
4	Q	0.190	0.790	
5	Qb	0.190	0.620	
6	Q1	0.190	0.440	
C	Q4	0.190	0.270	
2	GND	0.590	0.150	
Ð	O <sub>SC</sub> OUT2	0.950	0.150	
10	O <sub>SC</sub> OUT1	1.270	0.150	
11	O <sub>SC</sub> IN	1.310	0.340	
12	MR	1.310	0.650	
13	Q9	1.310	0.860	
14	Q8	1.310	1.050	
15	Q10	1.310	1.220	
16	V <sub>CC</sub>	0.880	1.350	
CON	NECT CHIP BA	CK TO V <sub>CC</sub> C	R FLOAT	

## Logic Diagram



### **Function Table**

CLO	СК	RESET	OUTPUT STAGE
_	_	L	NO CHANGE
	_	L	ADVANCE TO NEXT STATE
Х		Н	ALL OUTPUTS ARE LOW





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## Pad Descriptions

#### **INPUTS**

#### Osc IN (Pad 11)

Negative-edge triggering clock input. A high-to-low transition on this input advances the state of the counter. Osc IN hay be driven by an external clock source.

#### **CONTROL INPUTS**

#### MR (Pad 12)

Active—high reset. A high level applied to this input asynchronously resets the counter to its zero state (forcing at Q outputs low) and disables the oscillator.

#### **OUTPUTS**

Q4—Q10, Q12–Q14 (Pads 7, 5, 4, 6, 13, 15, 1, 2, 3) Active–high outputs. Each Qn output divided the Clock input frequency by 2<sup>N</sup>. The user should note the Q1, Q2, Q3 and Q11 are not available as outputs.

#### Osc OUT1, Osc OUT2 (Pads 9, 10)

Oscillator outputs. These pads are used in conjunction with Osc IN and the external components to form an oscillator. When Osc IN is being driven with an external clock source, Osc OUT1 and Osc OUT2 must be left open circuited. With the crystal oscillator in RC configuration, Osc OUT2 must be left open circuited.

## Absolute Maximum Ratings<sup>1</sup>

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V <sub>cc</sub>	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> +0.5	V
DC Output Voltage	V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> +0.5	V
DC Input Current, per pad	I <sub>IN</sub>	±20	mA
DC Output Current, per pad	I <sub>OUT</sub>	±25	mA
DC V <sub>CC</sub> or GND Current, per pad	I <sub>cc</sub>	±50	mA
Power Dissipation in Still Air <sup>2</sup>	P <sub>D</sub>	750	mW
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°C

<sup>1.</sup> Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

# Recommended Operating Conditions<sup>3</sup> (Voltages referenced to GND)

PA RAMETER	SYMBOL	MIN	MAX	UNITS	
DC Supply Votage	V <sub>CC</sub>	2 <sup>4</sup>	6	V	
DC Input or Du out Voltage	V <sub>IN</sub> ,V <sub>OUT</sub>	0	V <sub>CC</sub>	V	
Operating emperature Ra	T <sub>J</sub>	0	+85	°C	
**	V <sub>CC</sub> = 2.0V		0	1000	ns
Input Rise or Fall Times $V_{CC} = 4.5V$		t <sub>r</sub> , t <sub>f</sub>	0	500	
	V <sub>CC</sub> = 6.0V		0	400	

<sup>3.</sup> This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{IN}$  and  $V_{OUT}$  should be constrained to the range  $GND \le (V_{IN} \text{ or } V_{OUT}) \le V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

<sup>4.</sup> The oscillator is guaranteed to function at 2.5 V minimum. However, parametrics are tested at 2.0V by driving Pad 11 with an external clock source.





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## DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V <sub>cc</sub> CONDITIONS		LIMI	rs	DNITS		
	STWIDOL	▼ CC	CONDITIONS	25°C	85°C	FULL RANGE <sup>5</sup>	0.113	
Minimum High-Level Input Voltage		2.0V	V <sub>OUT</sub> = 0.1V or V <sub>CC</sub> -0.1V	1.5	1.5	1.5		
	V <sub>IH</sub>	3.0V		2.1	2.1	2.4	V	
	V IH	4.5V	I <sub>OUT</sub>   ≤ 20μA	3.15	3.15	3.15		
		6.0V		4.2	4.2	2		
		2.0V		0.5	0.5	0.5		
Maximum Low-Level	V <sub>IL</sub>	3.0V	$V_{OUT} = 0.1V \text{ or}$ $V_{CC} - 0.1V$	0.9	0.9	0.9	V	
Input Voltage	VIL.	4.5V	I <sub>OUT</sub>   ≤ 20μA	1.35	1.35	1.35	•	
		6.0V	1 00.1	1.8	1.9	1.8		
		2.0V	\/ =\/ or\/	1.9	7.9	1.9		
Minimum High-Level Output Voltage (Q4–Q10, Q12–Q14)		4.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 20 \mu A$	4:4	4.4	4.4	V	
		6.0V	1.0011 = 15.1	5.9	5.9	5.9		
	V <sub>OH</sub>	3.0V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 2.4 \text{mA}$	2.48	2.34	2.34	V	
	Ţ	4.5V	$V_{IN} = V_{IH} \text{ or } V_{L}$ $ I_{OUT}  \le 4.0 \text{mA}$	3.98	3.84	3.84		
		6.0V	$V_{IN} = V_{IL} \text{ or } V_{IL}$ $V_{IJT} = 5.2 \text{ mA}$	5.48	5.34	5.34		
		2.0V	$V_{\text{IN}} = V_{\text{IH}} \text{ or } V_{\text{IL}}$ $V_{\text{OUT}}   \le 20 \mu \text{A}$	0.1	0.1	0.1	V	
		4.5V		0.1	0.1	0.1		
		6.01		0.1	0.1	0.1		
Maximum Low-Level Output Voltage	V <sub>OL</sub>	307	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 2.4 \text{mA}$	0.26	0.33	0.33		
(Q4–Q10, Q12–Q14)	8	4.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 4.0 \text{mA}$	0.26	0.33	0.33	V	
		6.0V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $\left  I_{OUT} \right  \le 5.2 \text{mA}$	0.26	0.33	0.33		
		2.0V	V = V or CND	1.9	1.9	1.9		
<b>~</b>	<u> </u>	4.5V	$V_{IN} = V_{CC} \text{ or GND}$ $ I_{OUT}  \le 20\mu\text{A}$	4.4	4.4	4.4	V	
		6.0V	1.001  = 20p/ (	5.9	5.9	5.9		
Minimum, High-Level Output oltage (OscoUT1, OscoUT2)	V <sub>ОН</sub> 3	V <sub>OH</sub> 3.0V	3.0V	$V_{IN} = V_{CC} \text{ or GND}$ $ I_{OUT}  \le 0.7 \text{mA}$	2.48	2.34	2.34	
		4.5V	$V_{IN} = V_{CC}$ or GND $ I_{OUT}  \le 1.0$ mA	3.98	3.84	3.84	V	
		6.0V	$V_{IN} = V_{CC}$ or GND $ I_{OUT}  \le 1.3$ mA	5.48	5.34	5.34		

**5**. 0°C ≤ T<sub>J</sub> ≤ +85°C



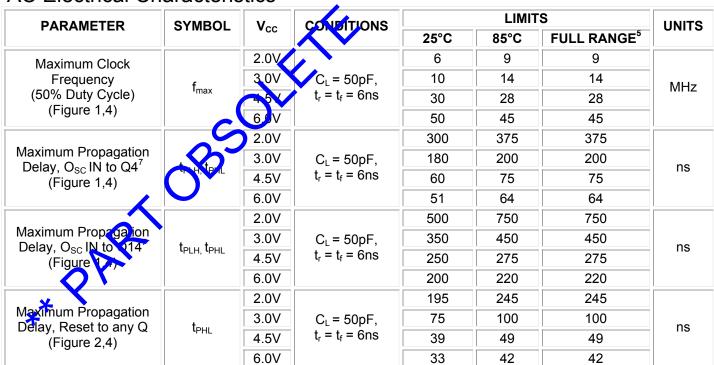


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### DC Electrical Characteristics Continued (Voltages referenced to GND)

PARAMETER	SYMBOL	V <sub>cc</sub> CONDITIONS		LIMITS			
	OTHIDOL	▼00	Vec SONDITIONS	25°C	85°C	FULL RANGE <sup>5</sup>	UNITS
		2.0V	V = V or CND	0.1	0.1	0.1	V
		4.5V	$V_{IN} = V_{CC}$ or GND $I_{OUT}   \le 20 \mu A$	0.1	0.1	0.4	
		6.0V	1.0011 = = 0 1.001	0.1	0.1	0.1	
Maximum Low-Level Output Voltage (OscOUT1, OscOUT2)	4.50	3.0V	$V_{IN} = V_{CC}$ or GND $ I_{OUT}  \le 0.7$ mA	0.26	0.33	0.33	
		4.5V	$V_{IN} = V_{CC}$ or GND $ I_{OUT}  \le 1.0$ mA	0.26	0.33	0.33	V
		6.0V	$V_{IN} = V_{CC}$ or GND $ I_{OUT}  \le 1.3$ mA	0.26	-0.33	0.33	
Maximum Input Leakage Current	I <sub>IN</sub>	6.0V	V <sub>IN</sub> = V <sub>CC</sub> or GND	±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Current	I <sub>CC</sub>	6.0V	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0\mu A$	4	80	80	μA

## AC Electrical Characteristics<sup>6</sup>



<sup>6.</sup> Not production tested in die form, characterized by chip design and tested in package.

 $V_{CC}$  = 2.0 V:  $t_P$  = [93.7 + 59.3 (n–1)] ns  $V_{CC}$  = 4.5 V:  $t_P$  = [30.25 + 14.6 (n–1)] ns

 $V_{CC}$  = 3.0 V:  $t_P$  = [61.5+ 34.4 (n-1)] ns

 $V_{CC} = 6.0 \text{ V: } t_P = [24.4 + 12 (n-1)] \text{ ns}$ 



<sup>7.</sup> For T<sub>J</sub> = 25°C and C<sub>L</sub> = 50 pF, typical propagation delay from Clock to other Q outputs may be calculated with the following equations:



# AC Electrical Characteristics continued<sup>6</sup>

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PARAMETER	SYMBOL	V <sub>cc</sub>	CONDITIONS	LIMITS			UNITS
		100	CONDITIONS	25°C	85°C	FULL RANGE <sup>5</sup>	
		2.0V		75	95	95	
Maximum Propagation Delay, Qn to Qn+1	t <sub>PLH</sub> , t <sub>PHL</sub>	3.0V	$C_L = 50pF,$	60	75	75	ns
(Figure 3,4)	PLH, PHL	4.5V	$t_r = t_f = 6$ ns	15	19	19	
( 5, /		6.0V		13	16	16	
Maximum Output	t <sub>TLH</sub> , t <sub>THL</sub>	2.0V	$\begin{array}{c} \text{.0V} \\ \text{.5V} \end{array} \qquad \begin{array}{c} C_L = 50 \text{pF}, \\ t_r = t_f = 6 \text{ns} \end{array}$	75	95	95	ns
Transition Time,		3.0V		27	32	32	
any output		4.5V		15	13	19	
(Figure 1,4)		6.0V		13		16	
Maximum Input Capacitance	C <sub>IN</sub>	-	-	10		10	pF
Power Dissipation Capacitance <sup>8</sup>	C <sub>PD</sub>	-	T <sub>A</sub> = 25°C, V <sub>CC</sub> = 5.0V	$O_{\mu}$	<b>TYPIC</b> 35		pF

<sup>8.</sup> Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} \bigvee_{i=1}^{n} I_{CC} V_{CC}$ 

## Timing Requirements<sup>6</sup>

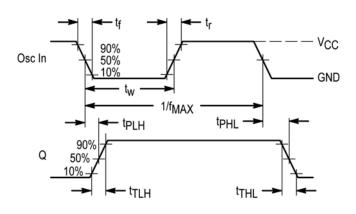
PARAMETER	SYMBOL	SYMBOL V <sub>cc</sub>	CONDITIONS		UNITS		
	OTHEOL			25°C	85°C	FULL RANGE <sup>5</sup>	Oitiio
Minimum Recovery		2.cV		100	125	125	
Time, Reset Inactive to	ton	3.0 V	$t_r = t_f = 6$ ns	75	100	100	ns
Clock (Figure 2)	l <sub>rec</sub> C	4.5V	t d one	20	25	25	110
(Figure 2)	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	6.0V		17	21	21	
	$\bigcirc$	2.0V		75	95	95	
Minimum Pulse Width, Clock	3.0V 4.5V 6.0V	3.0V	$t_r = t_f = 6$ ns	27	32	32	ns
(Figure 1)		4.5V		15	19	19	
		6.0V		13	16	16	
		2.0V	$t_r = t_f = 6$ ns	75	95	95	ns
Minimum Pilse Width,		3.0V		27	32	32	
(Figure 2)	-w	4.5V		15	19	19	
*		6.0V		13	16	16	
Maximum Input Rise and Fall Times (Figure 1)		2.0V		1000	1000	1000	
	3.0V	3.0V	$t_r = t_f = 6$ ns	800	800	800	ns
	प, प	$t_{r,} t_{f}$ 4.5V	η - η - 0115	500	500	500	110
		6.0V		400	400	400	



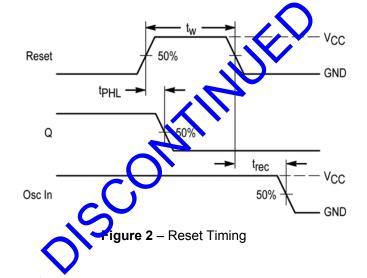


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## **Switching Waveforms**



**Figure 1** – Input to Output Propagation Delay & Timing



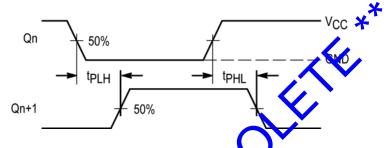
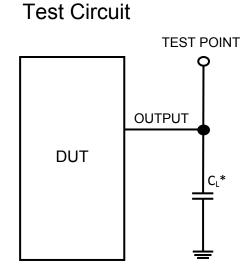


Figure 3 – Ripple output jiming



\* Includes all probe and jig capacitance

Figure 4 - Test Setup

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